

3/24/2009

### PRODUCT RELIABILITY REPORT FOR

## DS4432, Rev A1

# **Maxim Integrated Products**

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Prepared by:

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#### **Conclusion:**

The following qualification successfully meets the quality and reliability standards required of all Maxim products:

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In addition, Maxim's continuous reliability monitor program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards. The current status of the reliability monitor program can be viewed at http://www.maxim-ic.com/TechSupport /dsreliability.html.

#### **Device Description:**

A description of this device can be found in the product data sheet. You can find the product data sheet at http://dbserv.maxim-ic.com/l\_datasheet3.cfm.

#### **Reliability Derating:**

The Arrhenius model will be used to determine the acceleration factor for failure mechanisms that are temperature accelerated.

AfT = exp((Ea/k)\*(1/Tu - 1/Ts)) = tu/ts AfT = Acceleration factor due to Temperature tu = Time at use temperature (e.g. 55°C) ts = Time at stress temperature (e.g. 125°C) k = Boltzmann's Constant (8.617 x 10-5 eV/°K) Tu = Temperature at Use (°K) Ts = Temperature at Stress (°K) Ea = Activation Energy (e.g. 0.7 ev)

The activation energy of the failure mechanism is derived from either internal studies or industry accepted standards, or activation energy of 0.7ev will be used whenever actual failure mechanisms or their activation energies are unknown. All deratings will be done from the stress ambient temperature to the use ambient temperature.

An exponential model will be used to determine the acceleration factor for failure mechanisms, which are voltage accelerated.

AfV = exp(B\*(Vs - Vu)) AfV = Acceleration factor due to Voltage Vs = Stress Voltage (e.g. 7.0 volts) Vu = Maximum Operating Voltage (e.g. 5.5 volts) B = Constant related to failure mechanism type (e.g. 1.0, 2.4, 2.7, etc.)

The Constant, B, related to the failure mechanism is derived from either internal studies or industry accepted standards, or a B of 1.0 will be used whenever actual failure mechanisms or their B are unknown. All deratings will be done from the stress voltage to the maximum operating voltage. Failure rate data from the operating life test is reported using a Chi-Squared statistical model at the 60% or 90% confidence level (Cf).

The failure rate, Fr, is related to the acceleration during life test by:

Fr = X/(ts \* AfV \* AfT \* N \* 2)X = Chi-Sq statistical upper limit N = Life test sample size Failure Rates are reported in FITs (Failures in Time) or MTTF (Mean Time To Failure). The FIT rate is related to MTTF by:

MTTF = 1/Fr

NOTE: MTTF is frequently used interchangeably with MTBF.

The calculated failure rate for this device/process is:

FAILURE RATE:	MTTF (YRS):	16878	FITS:	6.8
	<b>DEVICE HOURS:</b>	143640	FAILS:	0

Only data from Operating Life or similar stresses are used for this calculation.

The parameters used to calculate this failure rate are as follows:

Cf: 60%	Ea: 0.7	B: 0	Tu: 25 °C	Vu: 5.5 Volts
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The reliability data follows. At the start of this data is the device information. The next section is the detailed reliability data for each stress. The reliability data section includes the latest data available and may contain some generic data. **Bold** Product Number denotes specific product data.

Device Informatio	n:								
Process:	E35MN-2P3M,NTC,DSD,PDESD,PDRES,CAP,ENPN,DPT,HTO,No Zero mas								
Passivation:	ion: TEOS Ox-Nit 2-Mask Laser/Pass for E35WM; Full BEOL at SA; PT only in Dallas								
Die Size:	59.84252 x 40.944882								
Number of Trans	sistors:	8400							
Interconnect:			um / 0.5	% Copper					
Gate Oxide Thicl	kness:	120 Å							
ESD HBM									
DESCRIPTION	DATE COI	DE/PRODU	CT/LOT	CONDITION	READ	POINT	QTY	FAILS	FA#
ESD SENSITIVITY	0844 <b>DS</b> 4	<b>1432</b> QJ	907640C	JESD22-A114 HBM 500 VOLTS	1	PUL'S	3	0	
ESD SENSITIVITY	0844 <b>DS</b> 4	4432 QJ	907640C	JESD22-A114 HBM 1000 VOLTS	1	PUL'S	3	0	
ESD SENSITIVITY	0844 <b>DS</b> 4	<b>1432</b> QJ	907640C	JESD22-A114 HBM 2000 VOLTS	1	PUL'S	3	0	
ESD SENSITIVITY	0844 <b>DS</b> 4			JESD22-A114 HBM 4000 VOLTS	1	PUL'S	3	0	
ESD SENSITIVITY	0844 <b>DS</b> 4	<b>1432</b> QJ9	907640C	JESD22-A114 HBM 8000 VOLTS	1	PUL'S	3	-	No FA
					Total:			3	
LATCH-UP									
DESCRIPTION DATE CODE/PRODUCT/LOT		CONDITION	READPOINT		QTY	FAILS	FA#		
LATCH-UP I	0844 <b>DS</b> 4	4432 QJS	907640C	JESD78A, I-TEST 125C			6	0	
LATCH-UP V	0844 <b>DS</b> 4	1432 QJS	907640C	JESD78A, V-SUPPLY TEST 125C			6	0	
					Total:	:		0	
OPERATING LIFE									
DESCRIPTION	DATE CO	DE/PRODU	CT/LOT	CONDITION	READ	OPOINT	QTY	FAILS	FA#
HIGH TEMP OP LIFE	0713 DS7	75LX QD	708619	125C, 3.7 VOLTS	1000	HRS	45	0	
HIGH TEMP OP LIFE	0717 DS2	2704R QJ7	733633A	125C, 5.5 VOLTS	1000	HRS	45	0	
HIGH TEMP OP LIFE	0804 DS4	1424 QJ8	804645A	125C, 5.5 VOLTS	1000	HRS	45	0	
Rev B, 1/3/08									

HIGH TEMP OP LIFE	0844 <b>DS4432</b>	QJ907640C	125C, 5.5V (PS	SA) & 3.0V (PSB)	192	HRS	45	0
					Total:			0
FAILURE RATE:	MTTF (YRS):		16878	FITS:	6.8			
	DEVICE H	OURS:	143640	FAILS:	0			